

L Number	Hits	Search Text	DB	Time stamp
1	3343854	semiconductor diode schottky led mos mosfet chip die ic (integrated adj circuit)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 09:09
2	611399	(insulative insulate insulating insulation insulated glass epoxy ceramic) with (substrate carrier board)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 09:10
3	207167	(semiconductor diode schottky led mos mosfet chip die ic (integrated adj circuit)) same ((insulative insulate insulating insulation insulated glass epoxy ceramic) with (substrate carrier board))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 09:11
4	71531	((semiconductor diode schottky led mos mosfet chip die ic (integrated adj circuit)) same ((insulative insulate insulating insulation insulated glass epoxy ceramic) with (substrate carrier board))) same (through hole via)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 09:11
5	275057	(electrode terminal pad) with (expose exposed exposing external)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 09:13
6	6324	((((semiconductor diode schottky led mos mosfet chip die ic (integrated adj circuit)) same ((insulative insulate insulating insulation insulated glass epoxy ceramic) with (substrate carrier board))) same (through hole via)) same ((electrode terminal pad) with (expose exposed exposing external) )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 09:13
7	998	(((((semiconductor diode schottky led mos mosfet chip die ic (integrated adj circuit)) same ((insulative insulate insulating insulation insulated glass epoxy ceramic) with (substrate carrier board))) same (through hole via)) same ((electrode terminal pad) with (expose exposed exposing external) )) same (encapsulated encapsulate encapsulation encapsulating resin mold molding mould moulding molded moulded)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 09:14